

## N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ)
100	0.058 at V <sub>GS</sub> = 10 V	18	13 nC

### FEATURES

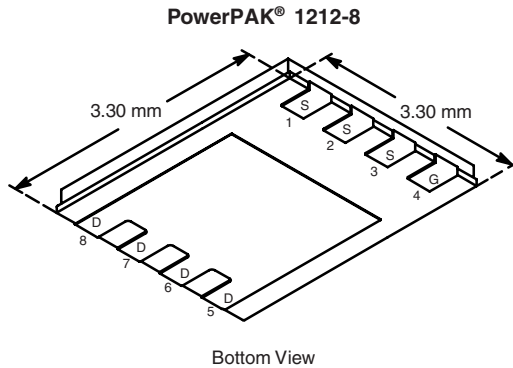
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % UIS Tested

### APPLICATIONS

- Primary Switch
- Isolated DC/DC Converters

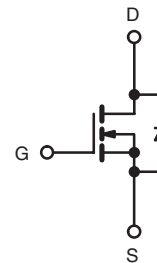


**RoHS**  
COMPLIANT



Bottom View

Ordering Information: Si7322DN-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	100	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	18 <sup>a</sup>	A
		T <sub>C</sub> = 70 °C	16 <sup>a</sup>	
		T <sub>A</sub> = 25 °C	5.5 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	4.4 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	20		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	18 <sup>a</sup>	
		T <sub>A</sub> = 25 °C	3.2 <sup>b, c</sup>	
Single Pulse Avalanche Current	I <sub>AS</sub>	19		
Single Pulse Avalanche Energy	E <sub>AS</sub>	18	mJ	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	52	W
		T <sub>C</sub> = 70 °C	33	
		T <sub>A</sub> = 25 °C	3.8 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	2.4 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	R <sub>thJA</sub>	26	33	°C/W	
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	1.9	2.4		

Notes:

- Package limited
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 81 °C/W.



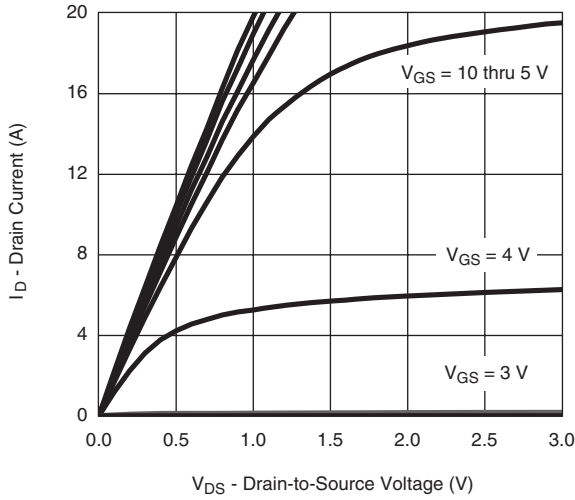
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	100			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		130		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 10		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2.5		4.4	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$ , $V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 5.5\text{ A}$		0.048	0.058	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 5.5\text{ A}$		10		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		750		pF
Output Capacitance	$C_{oss}$			80		
Reverse Transfer Capacitance	$C_{rss}$			25		
Total Gate Charge	$Q_g$	$V_{DS} = 50\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 5.5\text{ A}$		13	20	nC
Gate-Source Charge	$Q_{gs}$			3.7		
Gate-Drain Charge	$Q_{gd}$			3		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.3		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}$ , $R_L = 11.4\text{ }\Omega$ $I_D \cong 4.4\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$		10	15	ns
Rise Time	$t_r$			10	15	
Turn-Off Delay Time	$t_{d(off)}$			12	20	
Fall Time	$t_f$			10	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			18	A
Pulse Diode Forward Current	$I_{SM}$				20	
Body Diode Voltage	$V_{SD}$	$I_S = 4.4\text{ A}$ , $V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 4.4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$		40	60	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			70	105	nC
Reverse Recovery Fall Time	$t_a$			30		ns
Reverse Recovery Rise Time	$t_b$			10		

Notes:

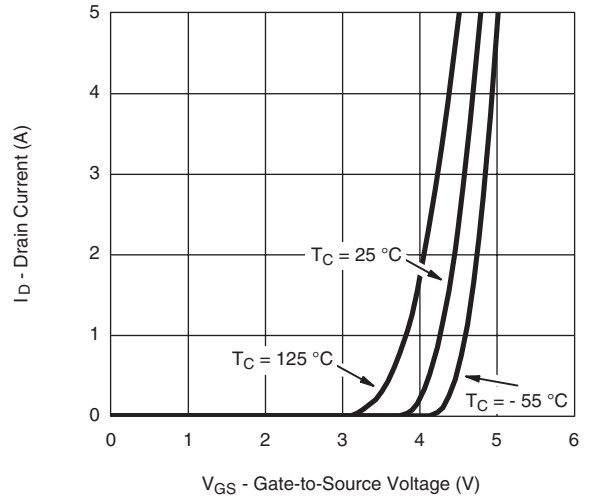
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

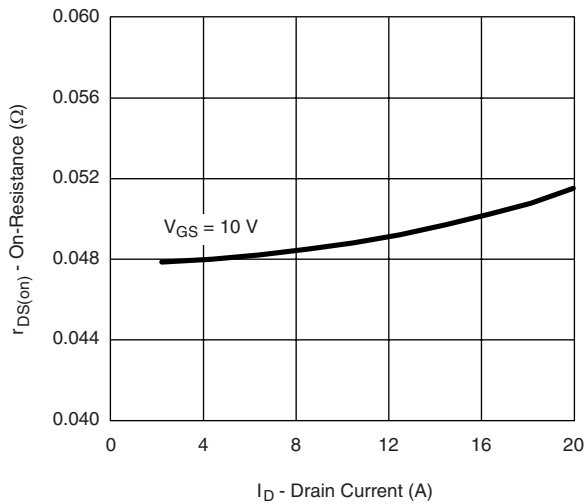
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



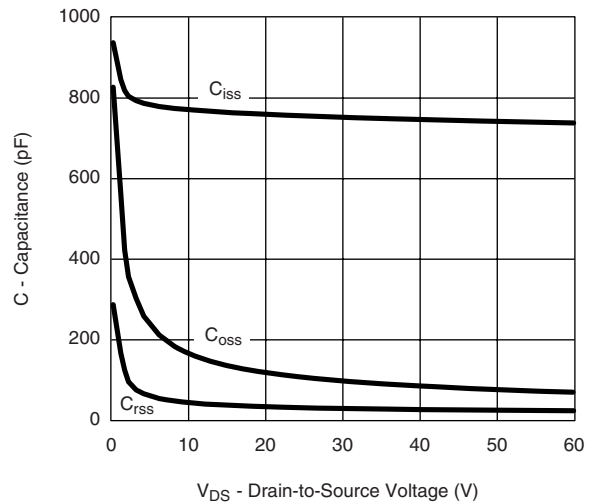
**Output Characteristics**



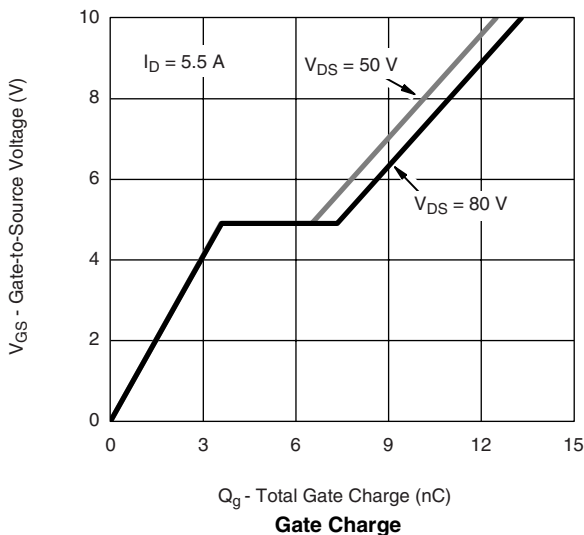
**Transfer Characteristics**



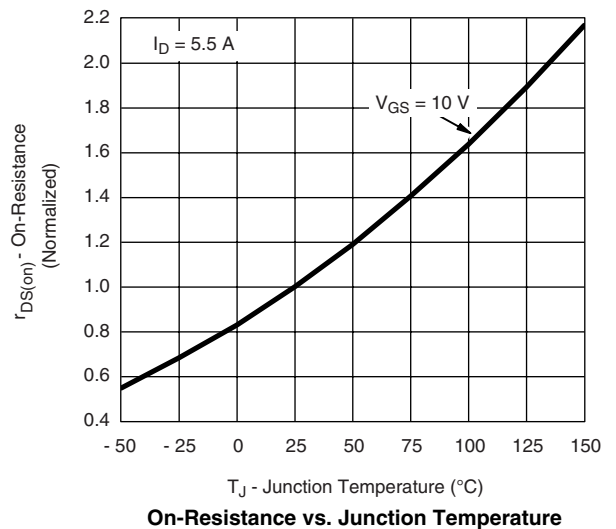
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



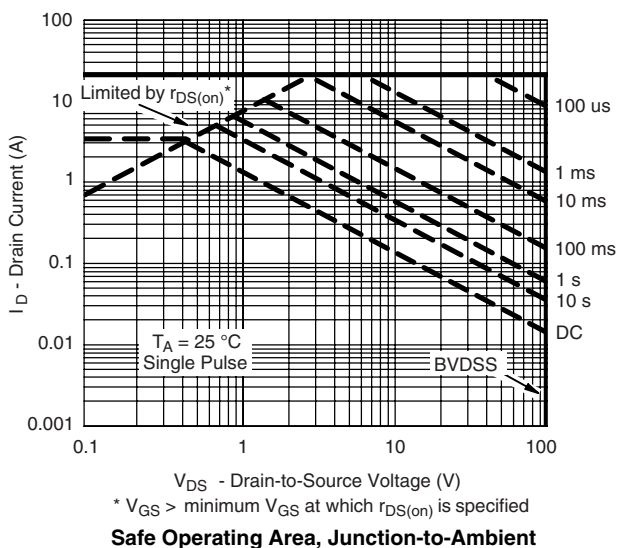
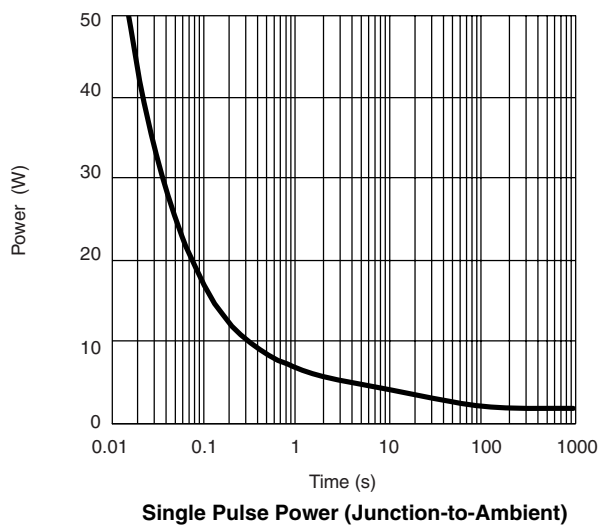
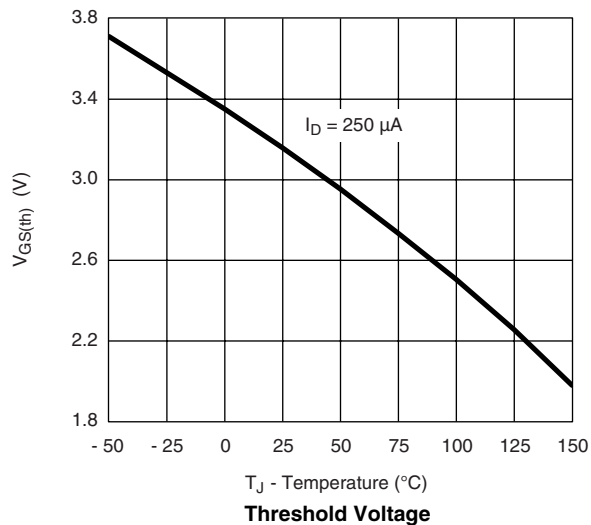
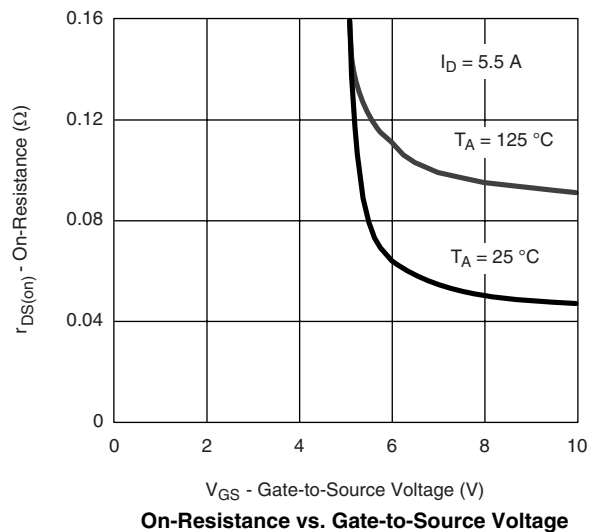
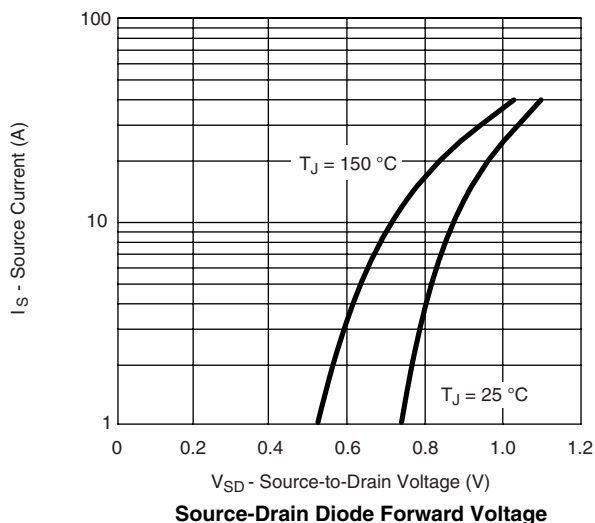
**Gate Charge**



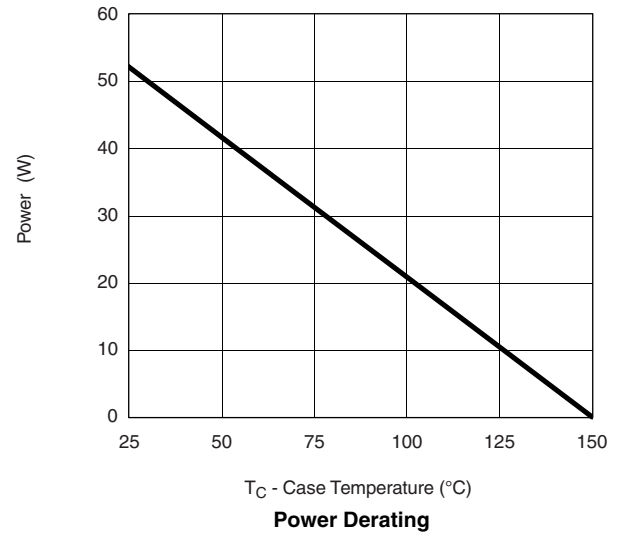
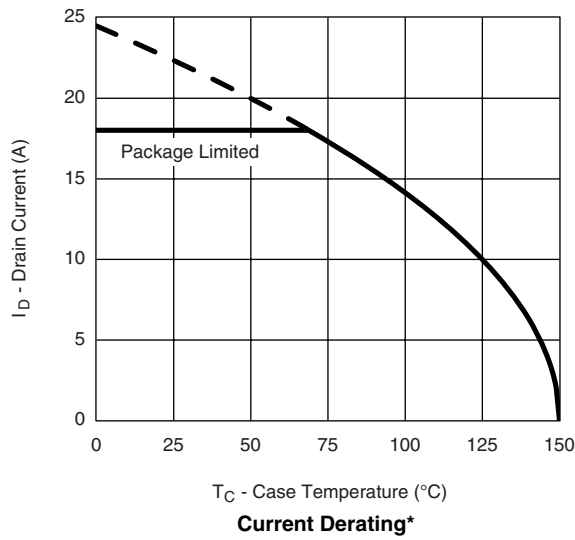
**On-Resistance vs. Junction Temperature**



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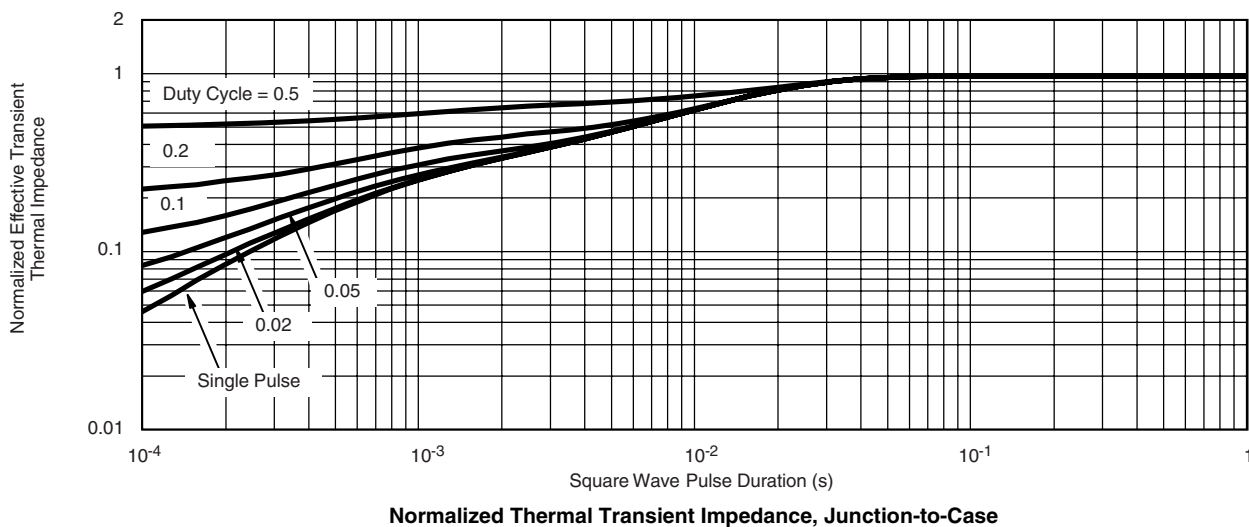
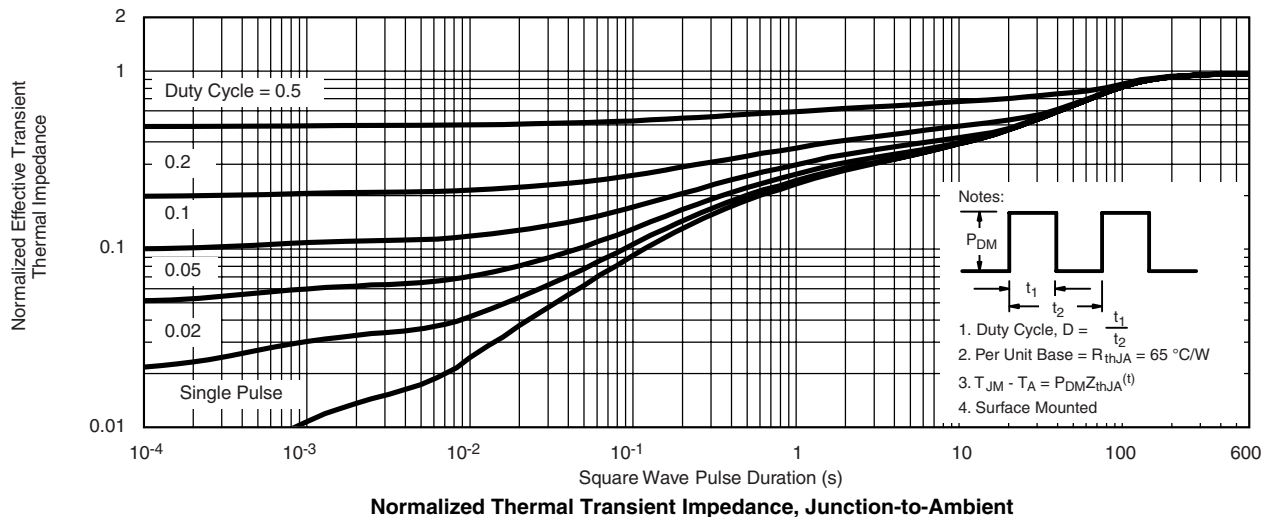
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

# Si7322DN

Vishay Siliconix



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?69638>.



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